

General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

Features

40V, 8.5A, $R_{DS(ON)} = 15m\Omega$ @ $V_{GS} = 10V$

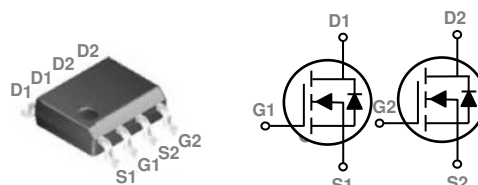
Improved dv/dt capability

Fast switching

Green Device Available

V_{DSS} 40 V
 I_D 8.5 A
 $R_{DS(ON)}$ 25 $m\Omega$

GK xxx
AO4882



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_c=25^\circ\text{C}$)	8.5	A
	Drain Current – Continuous ($T_c=100^\circ\text{C}$)	5	A
I_{DM}	Drain Current – Pulsed ¹	34	A
P_D	Power Dissipation ($T_c=25^\circ\text{C}$)	3.7	W
	Power Dissipation – Derate above 25°C	0.029	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	60	$^\circ\text{C} / \text{W}$

Electrical Characteristics (T_J=25°C unless otherwise specified)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	40	---	---	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =40V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =32V, V _{GS} =0V, T _J =125°C	---	---	10	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance ³	V _{GS} =10V, I _D =8A	---	15	19	mΩ
		V _{GS} =4.5V, I _D =5A	---	20	26	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	1.5	2.5	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =1A	---	3	---	S

Dynamic and switching Characteristics

Q _g	Total Gate Charge ^{3, 4}	V _{DS} =20V, V _{GS} =4.5V, I _D =5A	---	4.5	---	nC
Q _{gs}	Gate-Source Charge ^{3, 4}		---	1.5	---	
Q _{gd}	Gate-Drain Charge ^{3, 4}		---	1.9	---	
T _{d(on)}	Turn-On Delay Time ^{3, 4}	V _{DD} =20V, V _{GS} =4.5V, R _G =25Ω I _D =1A	---	3.2	---	ns
T _r	Rise Time ^{3, 4}		---	8.6	---	
T _{d(off)}	Turn-Off Delay Time ^{3, 4}		---	18	---	
T _f	Fall Time ^{3, 4}		---	6	---	
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, F=1MHz	---	420	---	pF
C _{oss}	Output Capacitance		---	65	---	
C _{rss}	Reverse Transfer Capacitance		---	40	---	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	8.5	A
I _{SM}	Pulsed Source Current ³		---	---	17	A
V _{SD}	Diode Forward Voltage ³	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=17A., R_G=25Ω, Starting T_J=25°C.
3. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.

RATING AND CHARACTERISTIC CURVES

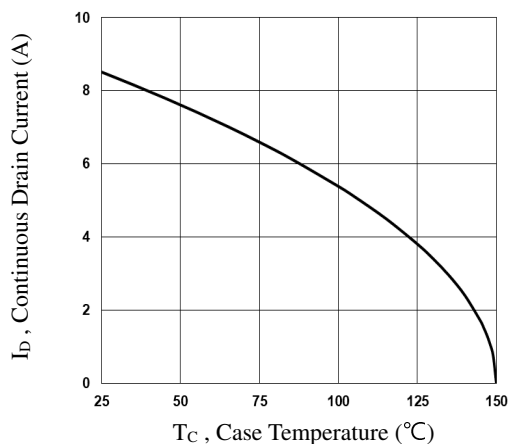


Fig.1 Continuous Drain Current vs. T_c

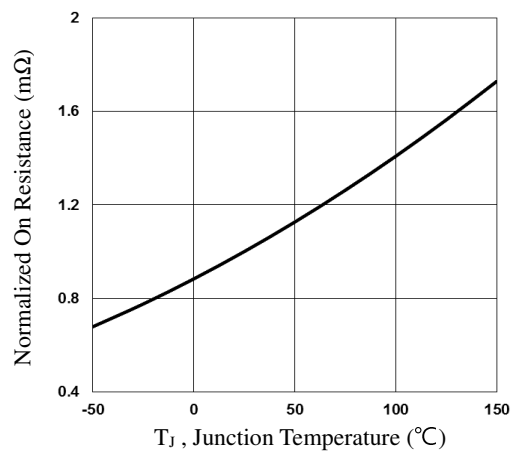


Fig.2 Normalized $R_{DS(on)}$ vs. T_j

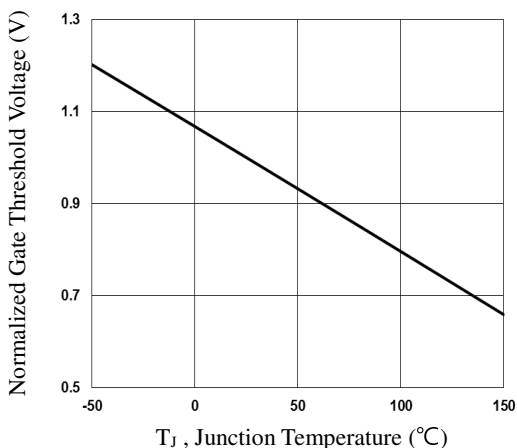


Fig.3 Normalized V_{th} vs. T_j

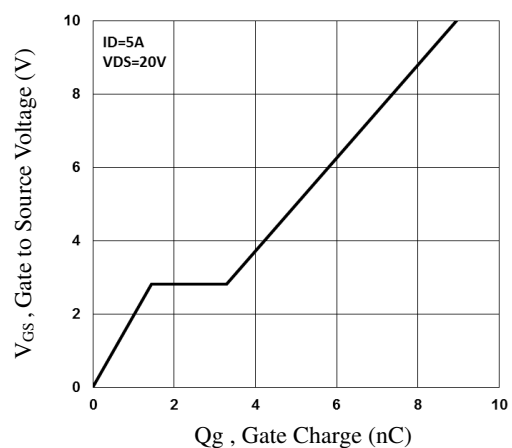


Fig.4 Gate Charge Waveform

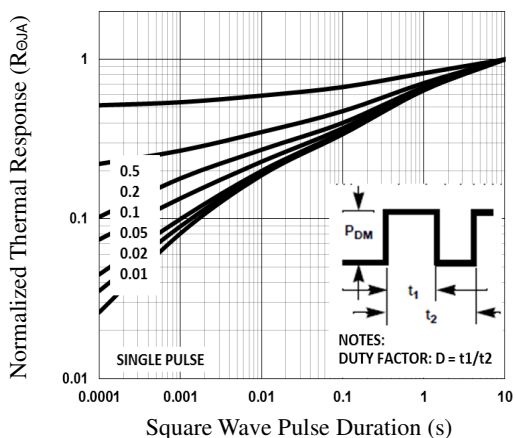


Fig.5 Normalized Transient Response

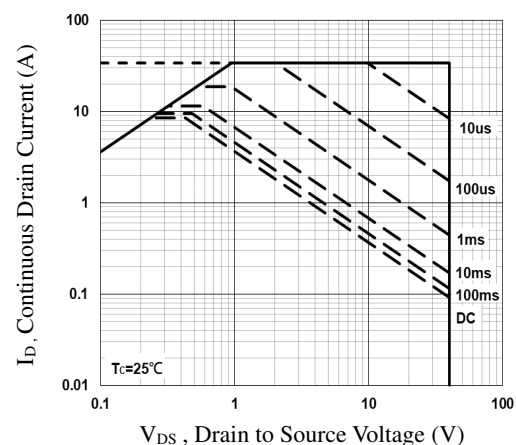


Fig.6 Maximum Safe Operation Area

RATING AND CHARACTERISTIC CURVES

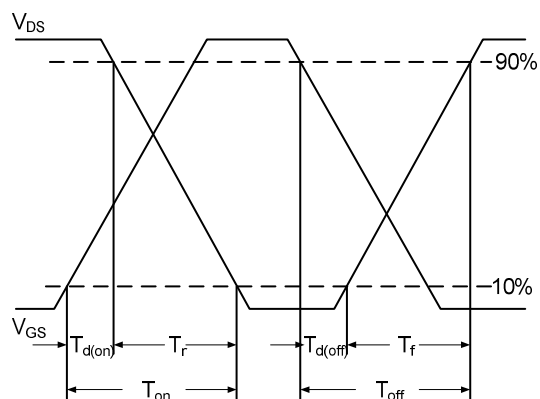
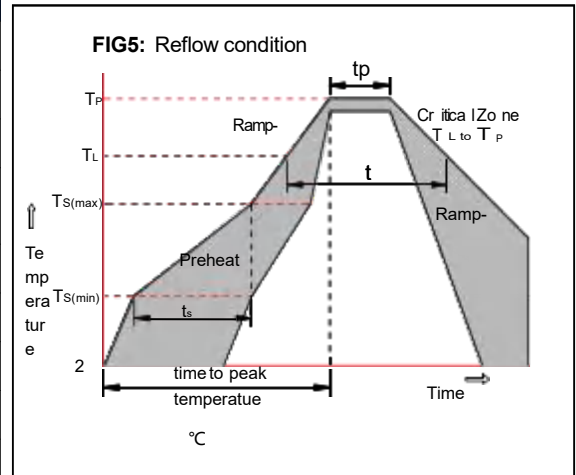


Fig.7 Switching Time Waveform

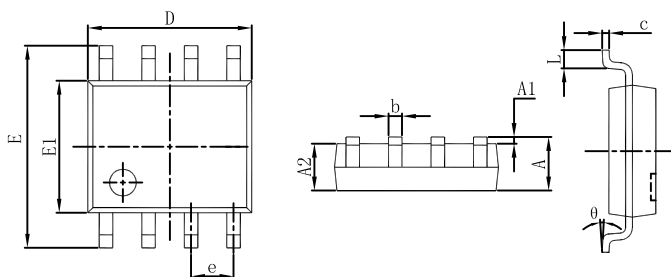
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_P)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C

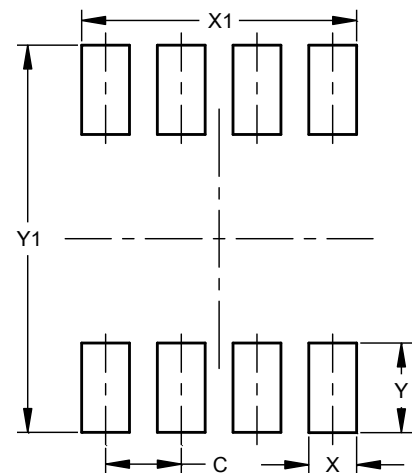


Package Dimensions & Suggested Pad Layout

SOP-8



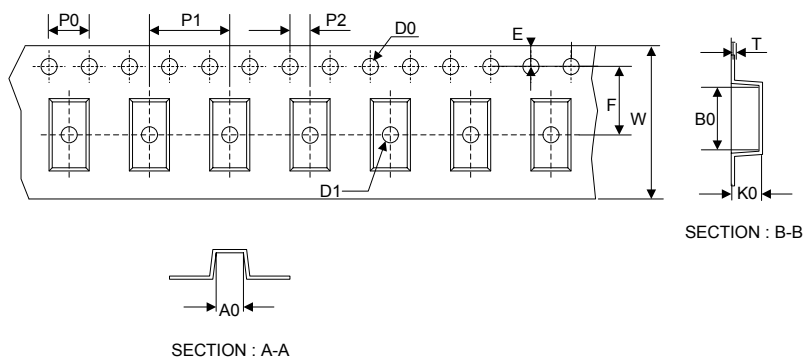
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Dimensions	Value (in mm)
C	1.27
X	0.70
X1	4.51
Y	2.00
Y1	7.00

Tape & reel specification

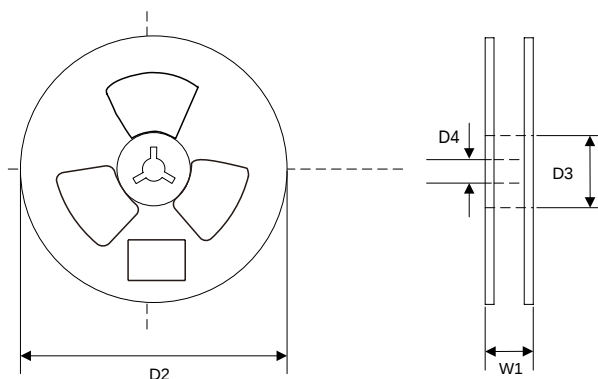
Tape



Symbol	Dimension (mm)
--------	----------------

P0	4.00±0.20
P1	8.00±0.20
P2	2.00±0.20
D0	1.55±0.20
D1	1.55±0.20
E	1.75±0.15
F	5.50±0.20
W	12.00±0.20
A0	7.00±0.20
B0	5.70±0.20
K0	1.35±0.20
T	0.23±0.20

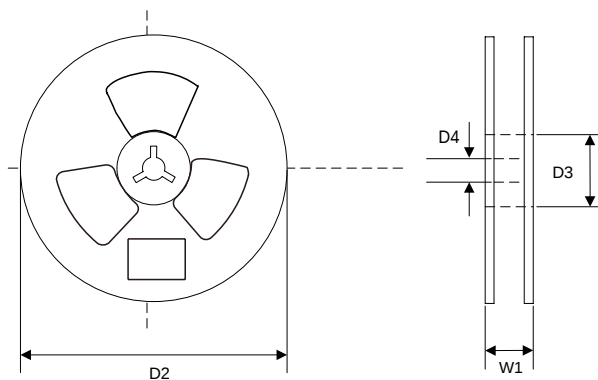
13" Reel



D2	330.0±5.0
D3	73Min.
D4	13.5±2.5
W1	16.0±3.0

Quantity: 3000PCS

13" Reel



D2	330.0±5.0
D3	73Min.
D4	13.5±2.5
W1	16.0±3.0

Quantity: 4000PCS